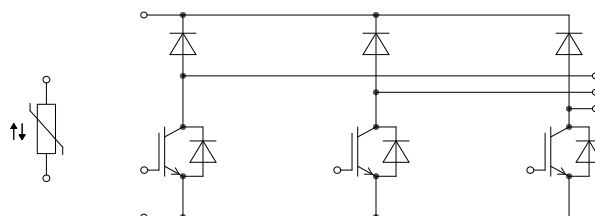
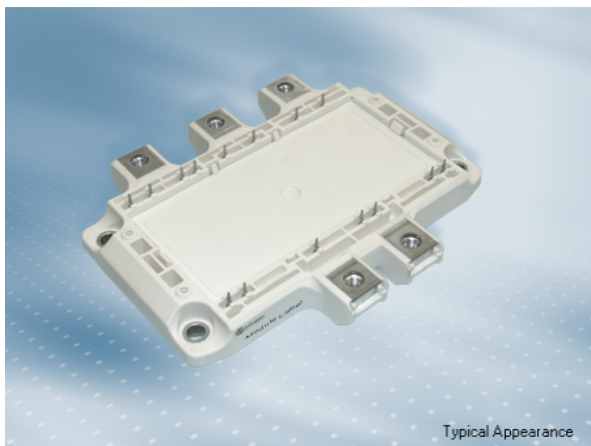


EconoPACK™4 模块 采用第四代沟槽栅/场终止IGBT4和发射极控制二极管 带有温度检测NTC  
EconoPACK™4 module with trench/fieldstop IGBT4 and Emitter Controlled Diode and NTC



$V_{CES} = 650V$   
 $I_{C\ nom} = 400A / I_{CRM} = 800A$

**典型应用**

- 斩波应用
- 电机传动
- 太阳能应用
- UPS系统

**电气特性**

- 增加阻断电压至650V
- 提高工作结温  $T_{vj\ op}$
- 沟槽栅IGBT4
- $T_{vj\ op} = 150^{\circ}C$
- $V_{CESat}$  带正温度系数

**机械特性**

- 2.5 kV 交流 1分钟 绝缘
- 高机械坚固性
- 集成NTC温度传感器
- 绝缘的基板
- 标封装

**Typical Applications**

- Chopper Applications
- Motor Drives
- Solar Applications
- UPS Systems

**Electrical Features**

- Increased blocking voltage capability to 650V
- Extended Operation Temperature  $T_{vj\ op}$
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$
- $V_{CESat}$  with positive Temperature Coefficient

**Mechanical Features**

- 2.5 kV AC 1min Insulation
- High mechanical robustness
- Integrated NTC temperature sensor
- Isolated Base Plate
- Standard Housing

**Module Label Code**

Barcode Code 128



DMX - Code



**Content of the Code**

**Digit**

Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: KY	date of publication: 2013-11-11	
approved by: MK	revision: 3.0	UL approved (E83335)

**IGBT, 制动-斩波器 / IGBT, Brake-Chopper**

**最大额定值 / Maximum Rated Values**

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	650	V
连续集电极直流电流 Continuous DC collector current	$T_C = 55^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	400 460	A A
模块端子的最大均方根电流 Maximum RMS module terminal current	$T_{Ct} = 90^{\circ}\text{C}$ $T_{Ct} = 50^{\circ}\text{C}$	$I_{RMS}$	240 300	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\text{ ms}$	$I_{CRM}$	800	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$P_{tot}$	1150	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

**特征值 / Characteristic Values**

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,55 1,70 1,75	1,95	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 4,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,1	5,8	6,4	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	4,30			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	1,0			$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	18,5			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,55			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			0,02	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,10 0,11 0,115			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,085 0,094 0,095			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,455 0,48 0,495			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,069 0,097 0,10			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 4200\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	5,50 7,95 8,25			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2600\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	20,0 24,0 25,0			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_p \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		$I_{SC}$	1500			A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$			0,13	K/W

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外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	$R_{\text{thCH}}$		0,064		K/W
在开关状态下温度 Temperature under switching conditions		$T_{\text{vj op}}$	-40		150	°C

## 二极管, 制动-斩波器 / Diode, Brake-Chopper

### 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{\text{vj}} = 25^\circ\text{C}$	$V_{\text{RRM}}$		650		V
连续正向直流电流 Continuous DC forward current		$I_{\text{F}}$		400		A
正向重复峰值电流 Repetitive peak forward current	$t_{\text{p}} = 1 \text{ ms}$	$I_{\text{FRM}}$		800		A
$I^2t$ -值 $I^2t$ - value	$V_{\text{R}} = 0 \text{ V}, t_{\text{p}} = 10 \text{ ms}, T_{\text{vj}} = 125^\circ\text{C}$ $V_{\text{R}} = 0 \text{ V}, t_{\text{p}} = 10 \text{ ms}, T_{\text{vj}} = 150^\circ\text{C}$	$I^2t$		8600 7600		$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

### 特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_{\text{F}} = 400 \text{ A}, V_{\text{GE}} = 0 \text{ V}$ $I_{\text{F}} = 400 \text{ A}, V_{\text{GE}} = 0 \text{ V}$ $I_{\text{F}} = 400 \text{ A}, V_{\text{GE}} = 0 \text{ V}$	$T_{\text{vj}} = 25^\circ\text{C}$ $T_{\text{vj}} = 125^\circ\text{C}$ $T_{\text{vj}} = 150^\circ\text{C}$	$V_{\text{F}}$	1,55 1,50 1,45	1,95	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_{\text{F}} = 400 \text{ A}, -di_{\text{F}}/dt = 4200 \text{ A}/\mu\text{s} (T_{\text{vj}}=150^\circ\text{C})$ $V_{\text{R}} = 300 \text{ V}$	$T_{\text{vj}} = 25^\circ\text{C}$ $T_{\text{vj}} = 125^\circ\text{C}$ $T_{\text{vj}} = 150^\circ\text{C}$	$I_{\text{RM}}$	130 205 215		A A A
恢复电荷 Recovered charge	$I_{\text{F}} = 400 \text{ A}, -di_{\text{F}}/dt = 4200 \text{ A}/\mu\text{s} (T_{\text{vj}}=150^\circ\text{C})$ $V_{\text{R}} = 300 \text{ V}$	$T_{\text{vj}} = 25^\circ\text{C}$ $T_{\text{vj}} = 125^\circ\text{C}$ $T_{\text{vj}} = 150^\circ\text{C}$	$Q_{\text{r}}$	10,0 26,5 27,5		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_{\text{F}} = 400 \text{ A}, -di_{\text{F}}/dt = 4200 \text{ A}/\mu\text{s} (T_{\text{vj}}=150^\circ\text{C})$ $V_{\text{R}} = 300 \text{ V}$	$T_{\text{vj}} = 25^\circ\text{C}$ $T_{\text{vj}} = 125^\circ\text{C}$ $T_{\text{vj}} = 150^\circ\text{C}$	$E_{\text{rec}}$	3,10 6,30 7,40		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{\text{thJC}}$		0,21	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{\text{thCH}}$	0,075		K/W
在开关状态下温度 Temperature under switching conditions			$T_{\text{vj op}}$	-40	150	°C

## 反向二极管 / Diode, Reverse

### 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{\text{vj}} = 25^\circ\text{C}$	$V_{\text{RRM}}$		650		V
连续正向直流电流 Continuous DC forward current		$I_{\text{F}}$		50		A
正向重复峰值电流 Repetitive peak forward current	$t_{\text{p}} = 1 \text{ ms}$	$I_{\text{FRM}}$		50		A
$I^2t$ -值 $I^2t$ - value	$V_{\text{R}} = 0 \text{ V}, t_{\text{p}} = 10 \text{ ms}, T_{\text{vj}} = 125^\circ\text{C}$ $V_{\text{R}} = 0 \text{ V}, t_{\text{p}} = 10 \text{ ms}, T_{\text{vj}} = 150^\circ\text{C}$	$I^2t$		330 300		$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

### 特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_{\text{F}} = 50 \text{ A}, V_{\text{GE}} = 0 \text{ V}$ $I_{\text{F}} = 50 \text{ A}, V_{\text{GE}} = 0 \text{ V}$ $I_{\text{F}} = 50 \text{ A}, V_{\text{GE}} = 0 \text{ V}$	$T_{\text{vj}} = 25^\circ\text{C}$ $T_{\text{vj}} = 125^\circ\text{C}$ $T_{\text{vj}} = 150^\circ\text{C}$	$V_{\text{F}}$	1,55 1,50 1,45	1,95	V V V
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{\text{thJC}}$		1,15	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{\text{thCH}}$	0,12		K/W
在开关状态下温度 Temperature under switching conditions			$T_{\text{vj op}}$	-40	150	°C

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**负温度系数热敏电阻 / NTC-Thermistor**  
**特征值 / Characteristic Values**

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^\circ\text{C}$	$R_{25}$		5,00		k $\Omega$
R100 偏差 Deviation of R100	$T_C = 100^\circ\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^\circ\text{C}$	$P_{25}$			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

**模块 / Module**

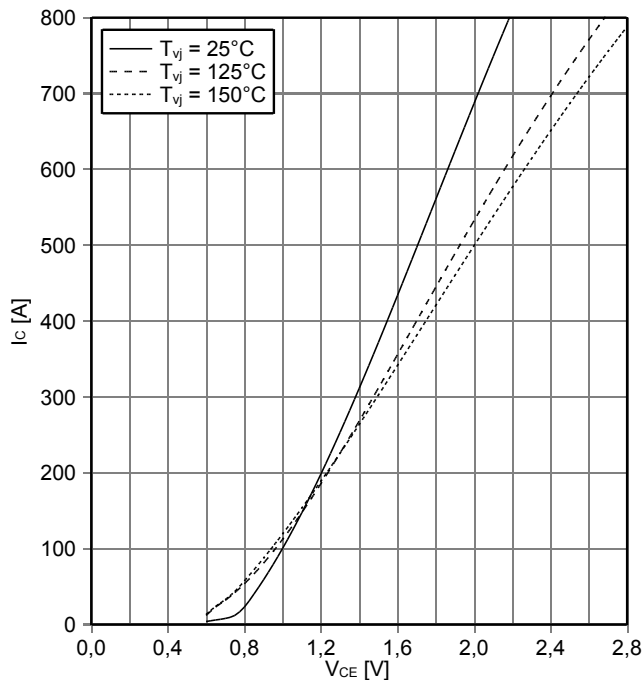
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	$V_{\text{ISOL}}$		2,5		kV
模块基板材料 Material of module baseplate				Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)			$\text{Al}_2\text{O}_3$		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal			15,0 12,5		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal			11,0 7,0		mm
相对电痕指数 Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
杂散电感, 模块 Stray inductance module		$L_{\text{SCE}}$		20		nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	$T_C = 25^\circ\text{C}$ , 每个开关 / per switch	$R_{\text{CC}+\text{EE}'}$		1,40		m $\Omega$
储存温度 Storage temperature		$T_{\text{stg}}$	-40		125	$^\circ\text{C}$
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00	-	6,00	Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,0	-	6,0	Nm
重量 Weight		G		400		g

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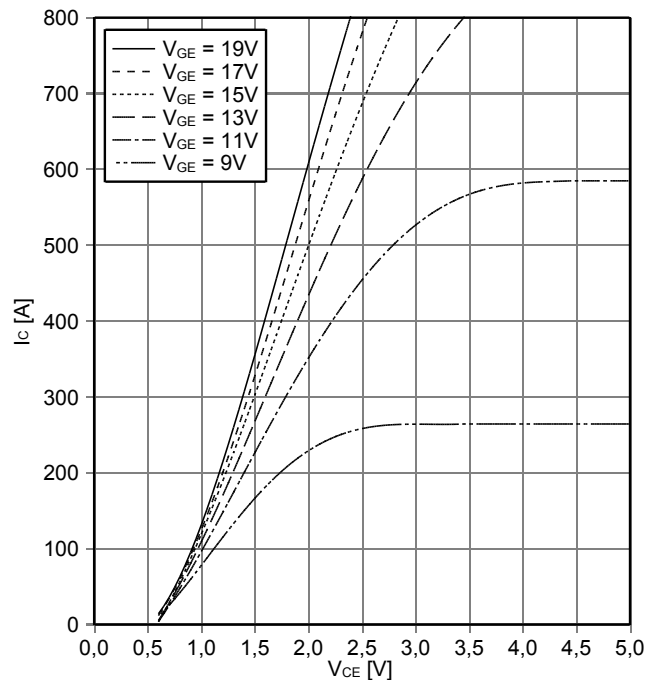
输出特性 IGBT, 制动-斩波器 (典型)  
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



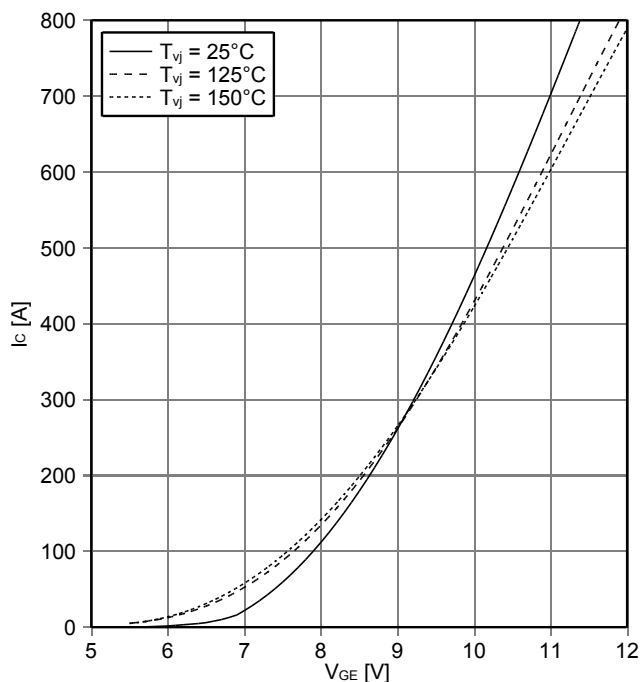
输出特性 IGBT, 制动-斩波器 (典型)  
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



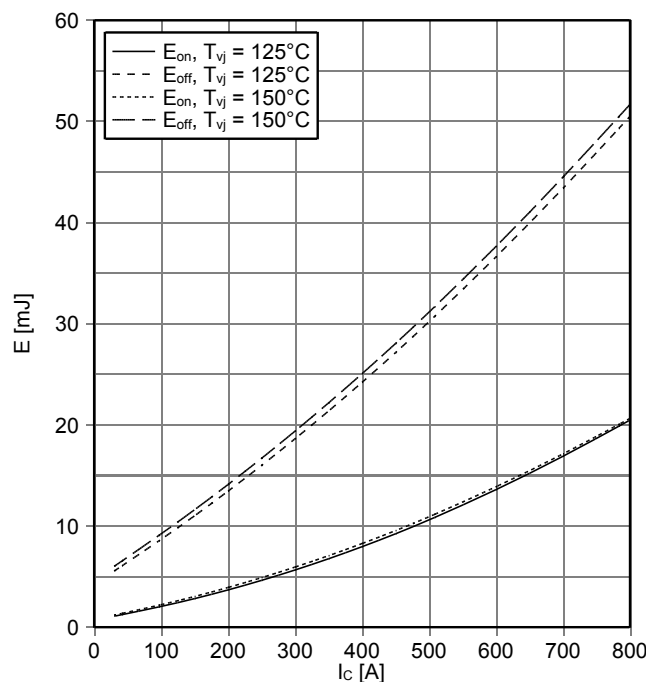
传输特性 IGBT, 制动-斩波器 (典型)  
transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 制动-斩波器 (典型)  
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 1.6\ \Omega$ ,  $R_{Goff} = 1.6\ \Omega$ ,  $V_{CE} = 300\text{ V}$

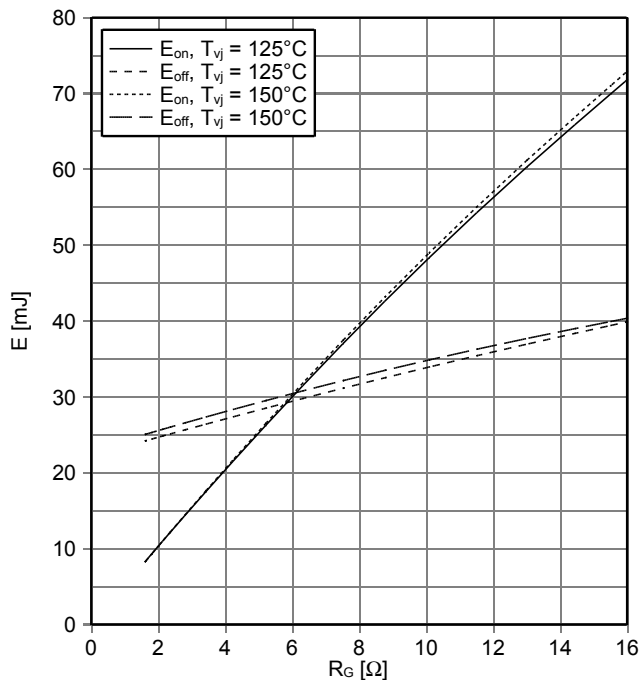


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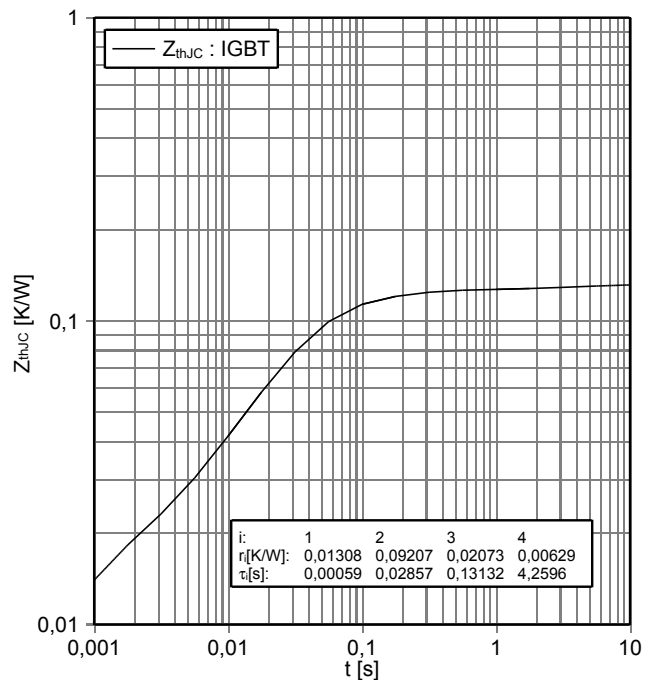
开关损耗 IGBT, 制动-斩波器 (典型)  
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}, I_C = 400\text{ A}, V_{CE} = 300\text{ V}$



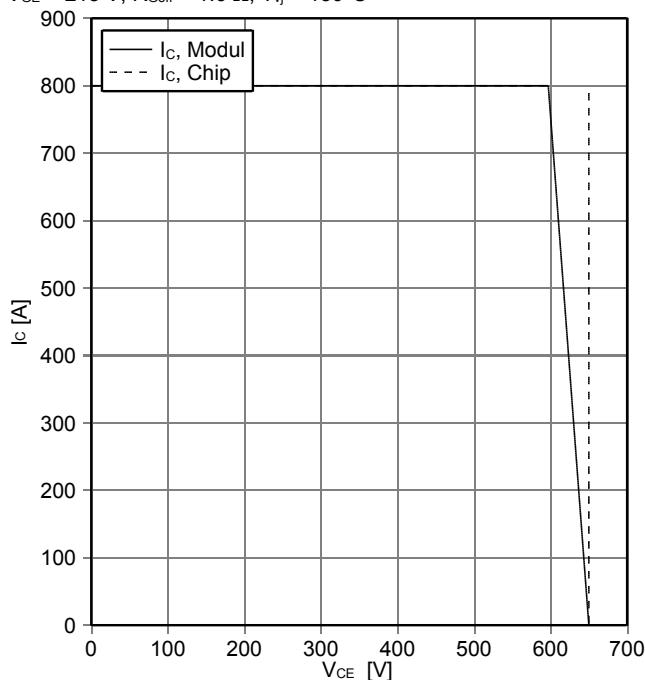
瞬态热阻抗 IGBT, 制动-斩波器  
transient thermal impedance IGBT, Brake-Chopper

$Z_{thJC} = f(t)$



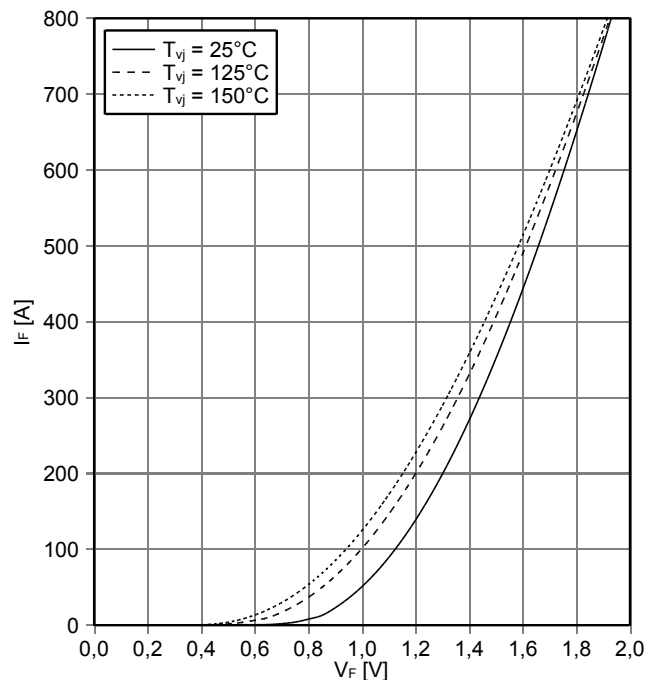
反偏安全工作区 IGBT, 制动-斩波器 (RBSOA)  
reverse bias safe operating area IGBT, Brake-Chopper (RBSOA)

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 1.6\ \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 制动-斩波器 (典型)  
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$

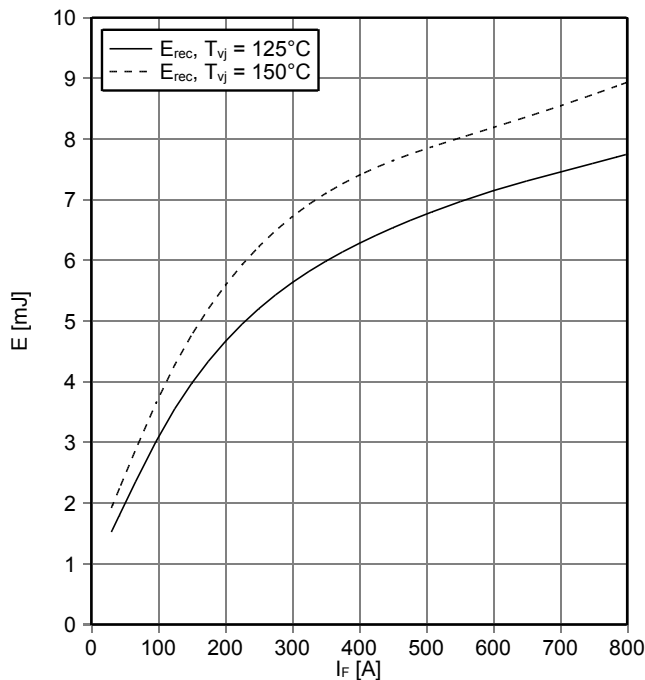


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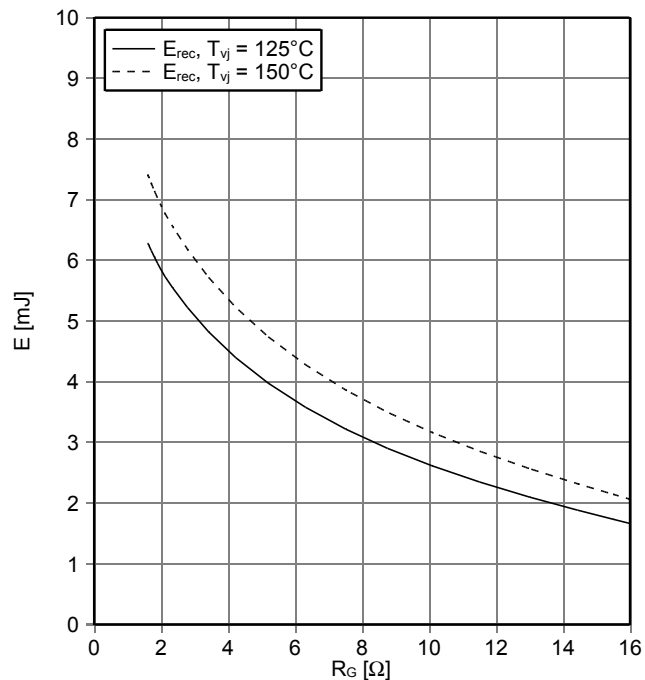
开关损耗 二极管，制动-斩波器 (典型)  
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 1.6 \Omega, V_{CE} = 300 V$



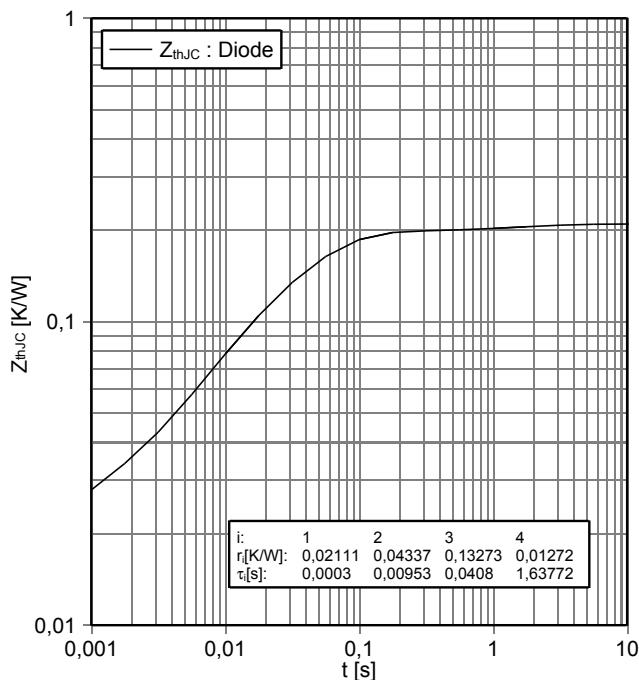
开关损耗 二极管，制动-斩波器 (典型)  
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(R_G)$   
 $I_F = 400 A, V_{CE} = 300 V$



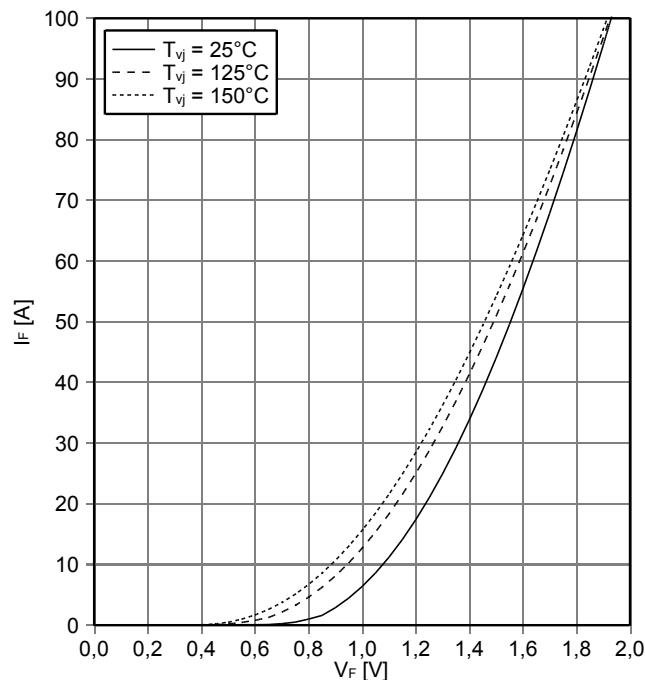
瞬态热阻抗 二极管，制动-斩波器  
transient thermal impedance Diode, Brake-Chopper

$Z_{thJC} = f(t)$



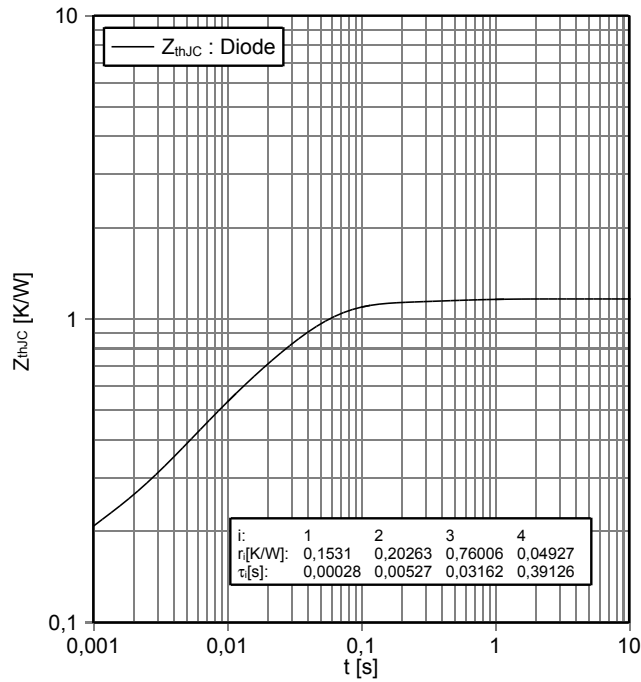
正向偏压特性 反向二极管 (典型)  
forward characteristic of Diode, Reverse (typical)

$I_F = f(V_F)$

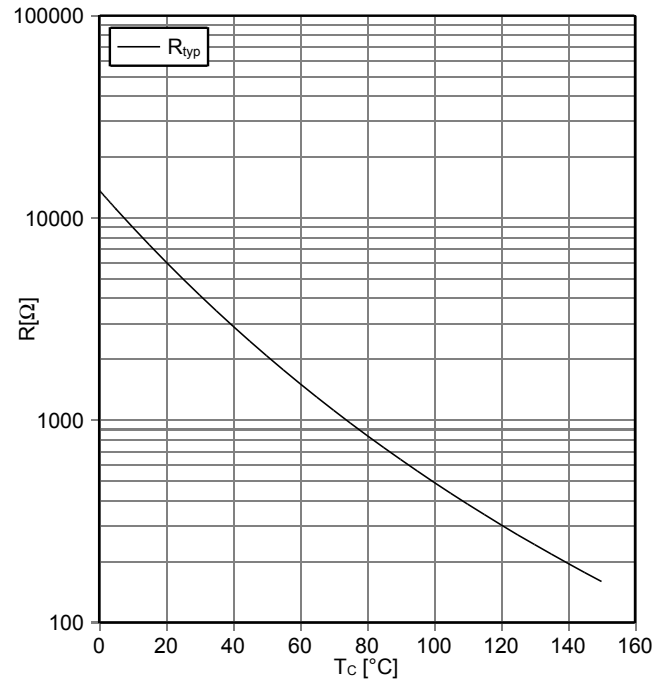


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瞬态热阻抗 反向二极管  
transient thermal impedance Diode, Reverse  
 $Z_{thJC} = f(t)$



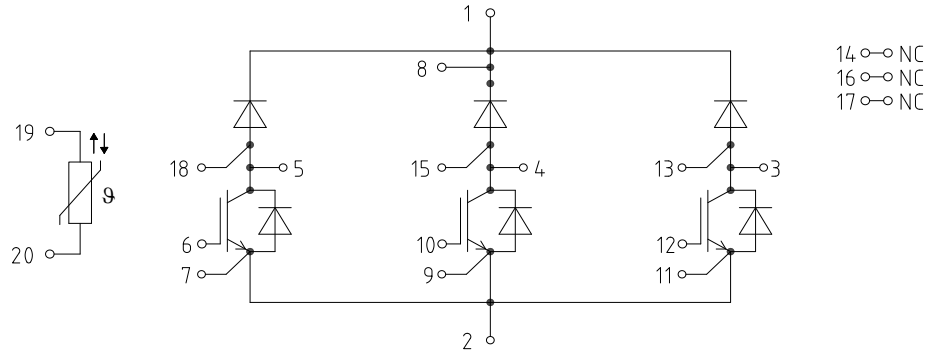
负温度系数热敏电阻 温度特性  
NTC-Thermistor-temperature characteristic (typical)  
 $R = f(T)$



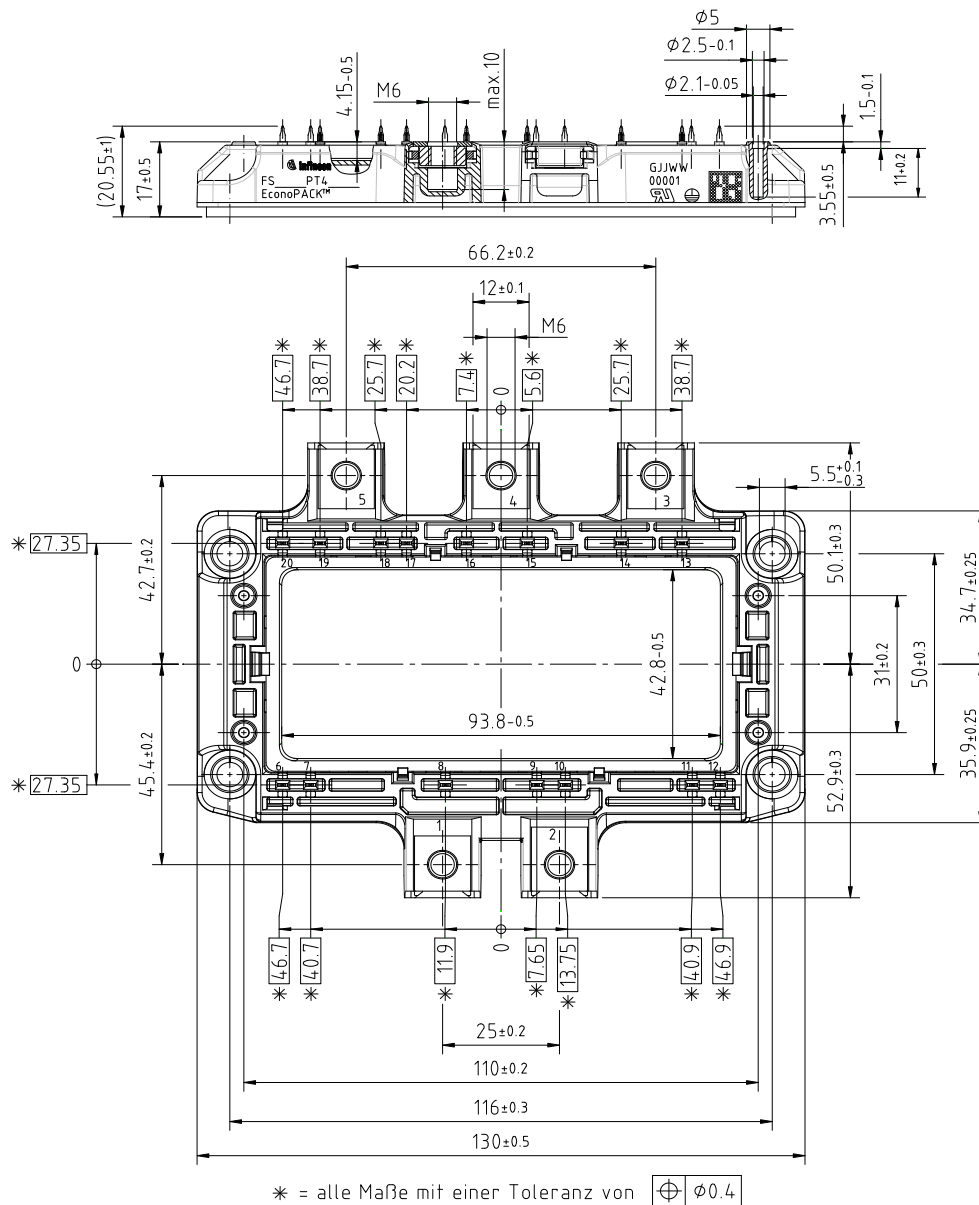
prepared by: KY	date of publication: 2013-11-11
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接线图 / circuit\_diagram\_headline



封装尺寸 / package outlines



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**使用条件和条款**

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- the conclusion of Quality Agreements;

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